

# MGFC42V5258

## 5.2 - 5.8GHz BAND 16W INTERNALLY MATCHED GaAs FET

### DESCRIPTION

The MGFC42V5258 is an internally impedance-matched GaAs power FET especially designed for use in 5.2 - 5.8 GHz band amplifiers. The hermetically sealed metal-ceramic package guarantees high reliability.

### FEATURES

- Class A operation
- Internally matched to 50(ohm) system
- High output power  
P1dB = 16W (TYP.) @ f=5.2 - 5.8 GHz
- High power gain  
GLP = 10.5 dB (TYP.) @ f=5.2 - 5.8GHz
- High power added efficiency  
P.A.E. = 31 % (TYP.) @ f=5.2 - 5.8GHz

### APPLICATION

5.2 - 5.8 GHz band power amplifier

### QUALITY GRADE

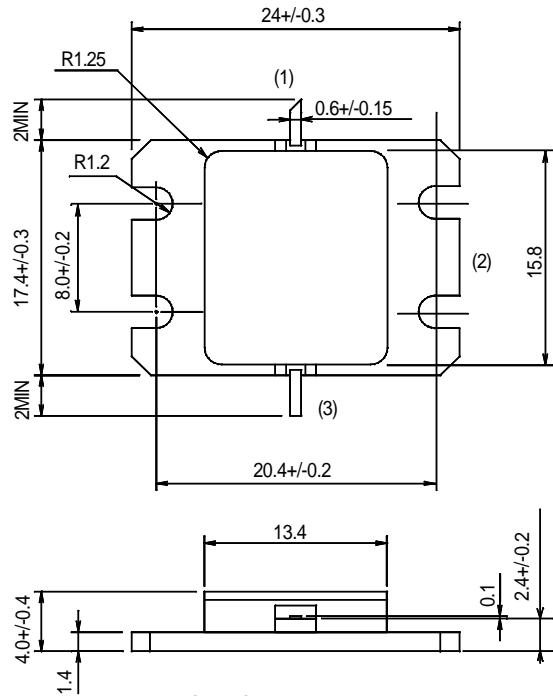
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### RECOMMENDED BIAS CONDITIONS

- VDS = 10 (V)
- ID = 4.5 (A)
- RG=25 (ohm)

### OUTLINE DRAWING

Unit: millimeters



GF-18

- (2): SOURCE (FLANGE)
- (3): DRAIN

### ABSOLUTE MAXIMUM RATINGS

(Ta=25deg.C)

Symbol	Parameter	Ratings	Unit
VGDO	Gate to drain voltage	-15	V
VGSO	Gate to source voltage	-15	V
ID	Drain current	15	A
IGR	Reverse gate current	-40	mA
IGF	Forward gate current	84	mA
PT	Total power dissipation *1	78.9	W
Tch	Channel temperature	175	deg.C
Tstg	Storage temperature	-65 / +175	deg.C

\*1 : Tc=25deg.C

< Keep safety first in your circuit designs! >  
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### ELECTRICAL CHARACTERISTICS

(Ta=25deg.C)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
IDSS	Saturated drain current	VDS = 3V , VGS = 0V	-	9	12	A
gm	Transconductance	VDS = 3V , ID = 4.4A	-	4	-	S
VGS(off)	Gate to source cut-off voltage	VDS = 3V , ID = 80mA	-2	-3	-4	V
P1dB	Output power at 1dB gain compression	VDS=10V, ID(RF off)=4.5A, f=5.2 - 5.8GHz	41.5	42.5	-	dBm
GLP	Linear power gain		8	10.5	-	dB
ID	Drain current		-	4.5	-	A
P.A.E.	Power added efficiency		-	31	-	%
Rth(ch-c)	Thermal resistance *1	delta Vf method	-	-	1.9	deg.C/W

\*1 : Channel-case

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